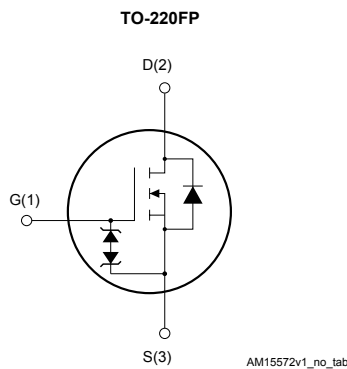


N-channel 600 V, 0.085 Ω typ., 34 A MDmesh DM2 Power MOSFET in a TO-220FP package



Product status links

[STF43N60DM2](#)

Product summary

Order code	STF43N60DM2
Marking	43N60DM2
Package	TO-220FP
Packing	Tube

Features

Order code	V_{DS} @ T_J max.	$R_{DS(on)}$ max.	I_D	P_{TOT}
STF43N60DM2	650 V	0.093 Ω	34 A	40 W

- Fast-recovery body diode
- Extremely low gate charge and input capacitance
- Low on-resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

Applications

- Switching applications

Description

This high-voltage N-channel Power MOSFET is part of the MDmesh DM2 fast-recovery diode series. It offers very low recovery charge (Q_{rr}) and time (t_{rr}) combined with low $R_{DS(on)}$, rendering it suitable for the most demanding high-efficiency converters and ideal for bridge topologies and ZVS phase-shift converters.

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±25	V
$I_D^{(1)}$	Drain current (continuous) at $T_{case} = 25\text{ °C}$	34	A
	Drain current (continuous) at $T_{case} = 100\text{ °C}$	21	
$I_{DM}^{(2)}$	Drain current (pulsed)	136	
P_{TOT}	Total power dissipation at $T_{case} = 25\text{ °C}$	40	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	50	V/ns
$dv/dt^{(4)}$	MOSFET dv/dt ruggedness	50	
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t = 1\text{ s}$; $T_C = 25\text{ °C}$)	2.5	kV
T_{stg}	Storage temperature range	-55 to 150	°C
T_j	Operating junction temperature range		°C

- Limited by maximum junction temperature.
- Pulse width is limited by safe operating area.
- $I_{SD} \leq 34$, $di/dt \leq 900\text{ A}/\mu\text{s}$, $V_{DS(peak)} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$
- $V_{DS} \leq 480\text{ V}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	3.13	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient	62.5	

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	6	A
E_{AR}	Single pulse avalanche energy (starting $T_j = 25\text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	800	mJ

2 Electrical characteristics

($T_{\text{case}} = 25\text{ °C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{DSS}}$	Drain-source breakdown voltage	$V_{\text{GS}} = 0\text{ V}$, $I_{\text{D}} = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current	$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 600\text{ V}$			1	μA
		$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 600\text{ V}$, $T_{\text{case}} = 125\text{ °C}$ ⁽¹⁾			100	μA
I_{GSS}	Gate-body leakage current	$V_{\text{DS}} = 0\text{ V}$, $V_{\text{GS}} = \pm 25\text{ V}$			± 5	μA
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{DS}} = V_{\text{GS}}$, $I_{\text{D}} = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{\text{DS(on)}}$	Static drain-source on-resistance	$V_{\text{GS}} = 10\text{ V}$, $I_{\text{D}} = 17\text{ A}$		0.085	0.093	Ω

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{\text{DS}} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{\text{GS}} = 0\text{ V}$	-	2500	-	pF
C_{oss}	Output capacitance		-	120	-	pF
C_{riss}	Reverse transfer capacitance		-	3	-	pF
$C_{\text{oss eq.}}$ ⁽¹⁾	Equivalent output capacitance	$V_{\text{DS}} = 0$ to 480 V , $f = 1\text{ MHz}$, $V_{\text{GS}} = 0\text{ V}$	-	200	-	pF
R_{G}	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_{\text{D}} = 0\text{ A}$	-	4	-	Ω
Q_{g}	Total gate charge	$V_{\text{DD}} = 480\text{ V}$, $I_{\text{D}} = 34\text{ A}$, $V_{\text{GS}} = 0$ to 10 V (see Figure 14. Test circuit for gate charge behavior)	-	56	-	nC
Q_{gs}	Gate-source charge		-	13	-	nC
Q_{gd}	Gate-drain charge		-	30	-	nC

1. $C_{\text{oss eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{\text{d(on)}}$	Turn-on delay time	$V_{\text{DD}} = 300\text{ V}$, $I_{\text{D}} = 25\text{ A}$, $R_{\text{G}} = 4.7\text{ }\Omega$, $V_{\text{GS}} = 10\text{ V}$ (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	29	-	ns
t_{r}	Rise time		-	27	-	ns
$t_{\text{d(off)}}$	Turn-off delay time		-	85	-	ns
t_{f}	Fall time		-	6	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$	Source-drain current		-		34	A
$I_{SDM}^{(2)}$	Source-drain current (pulsed)		-		136	A
$V_{SD}^{(3)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 34\text{ A}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 34\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	120		ns
Q_{rr}	Reverse recovery charge		-	0.6		μC
I_{RRM}	Reverse recovery current		-	10.4		A
t_{rr}	Reverse recovery time	$I_{SD} = 34\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	240		ns
Q_{rr}	Reverse recovery charge		-	2.4		μC
I_{RRM}	Reverse recovery current		-	20.5		A

1. Limited by maximum junction temperature.
2. Pulse width is limited by safe operating area.
3. Pulse test: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

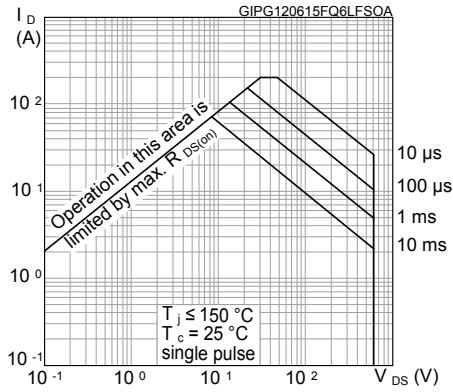


Figure 2. Thermal impedance

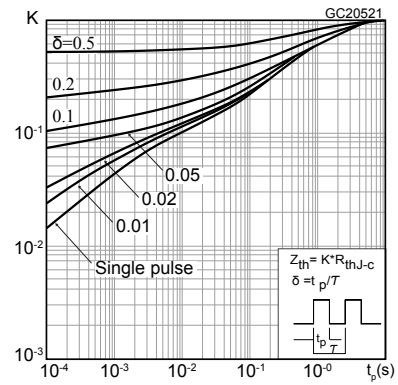


Figure 3. Output characteristics

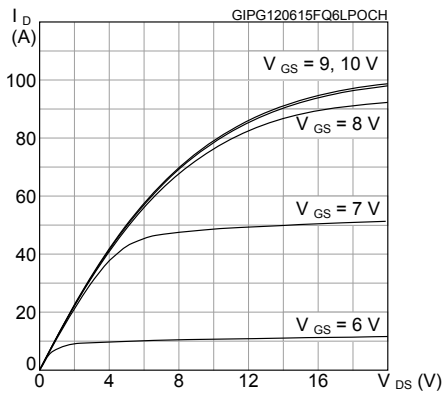


Figure 4. Transfer characteristics

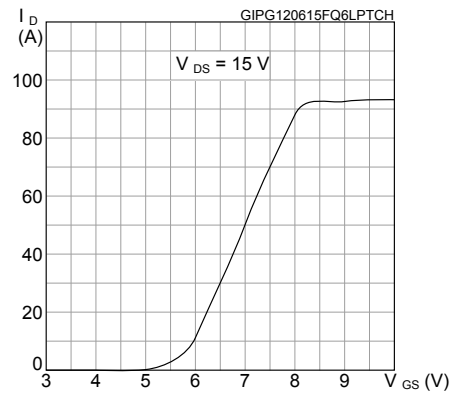


Figure 5. Gate charge vs gate-source voltage

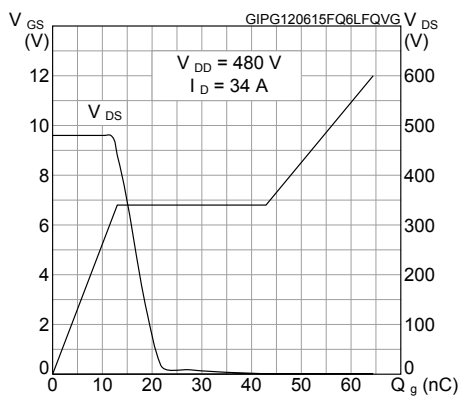


Figure 6. Static drain-source on-resistance

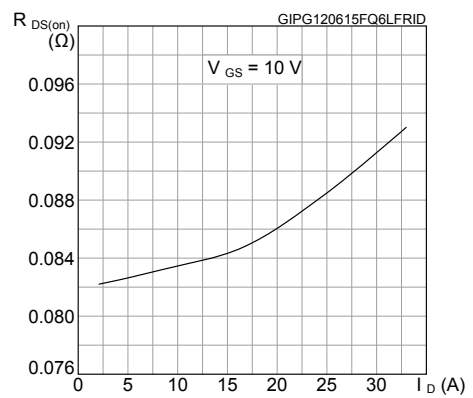


Figure 7. Capacitance variations

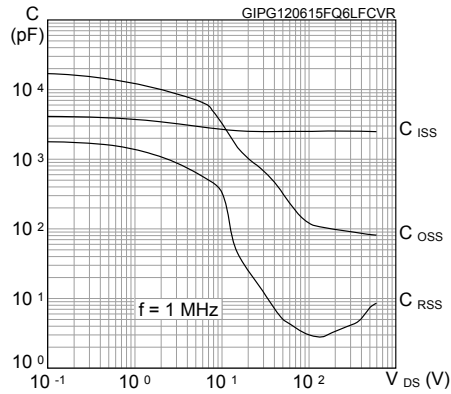


Figure 8. Normalized gate threshold voltage vs temperature

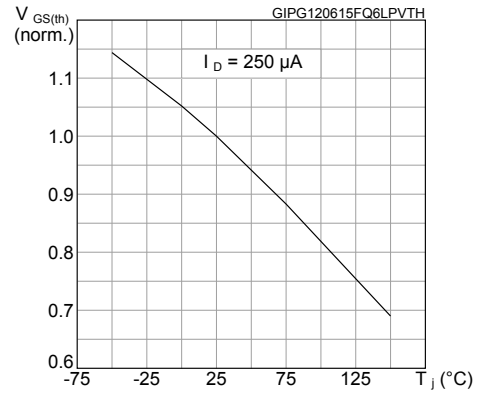


Figure 9. Normalized on-resistance vs temperature

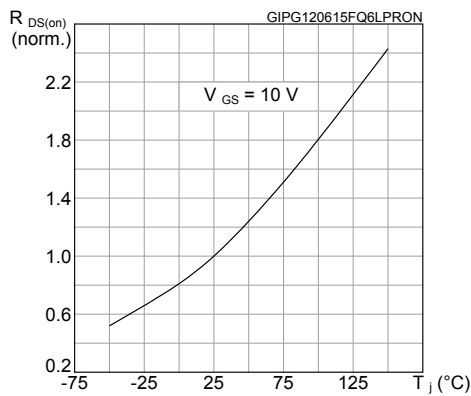


Figure 10. Normalized V_{(BR)DSS} vs temperature

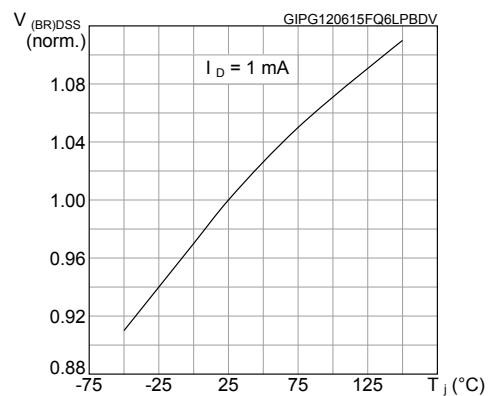


Figure 11. Output capacitance stored energy

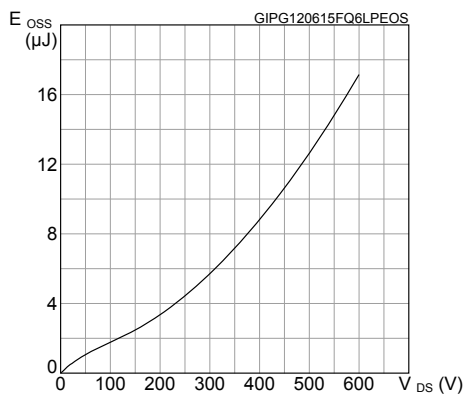
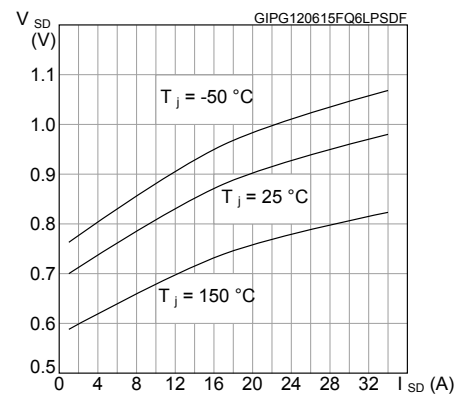
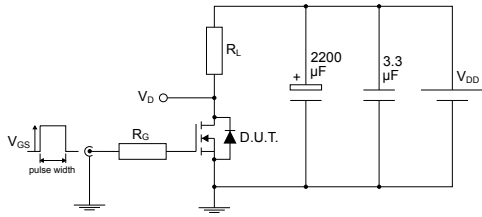


Figure 12. Source-drain diode forward characteristics



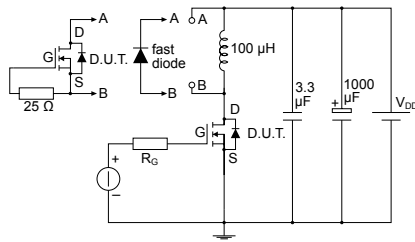
3 Test circuits

Figure 13. Test circuit for resistive load switching times


AM01468v1

Figure 14. Test circuit for gate charge behavior


AM01469v1

Figure 15. Test circuit for inductive load switching and diode recovery times


AM01470v1

Figure 16. Unclamped inductive load test circuit


AM01471v1

Figure 17. Unclamped inductive waveform


AM01472v1

Figure 18. Switching time waveform

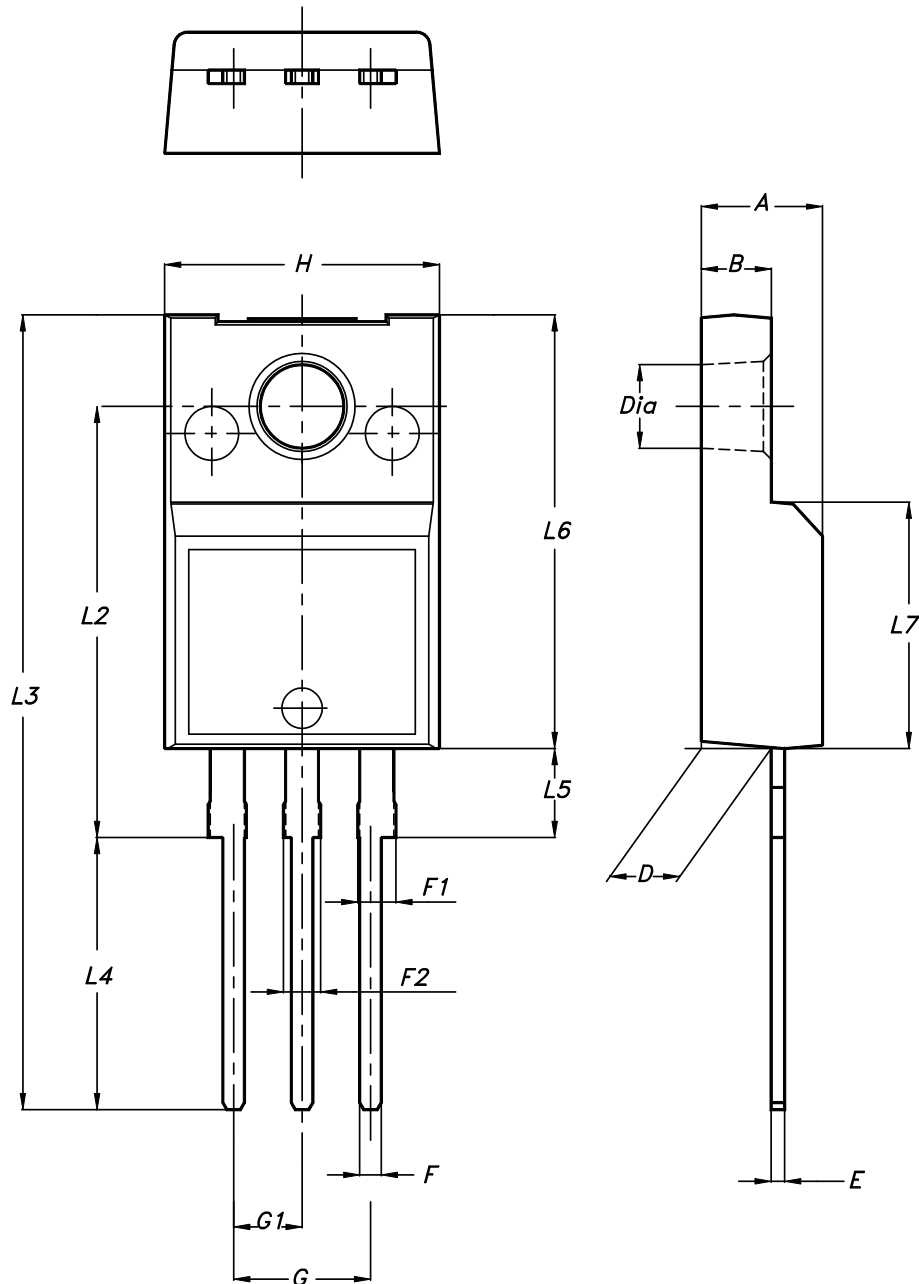

AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-220FP package information

Figure 19. TO-220FP package outline



7012510_Rev_13_B

Table 8. TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

Revision history

Table 9. Document revision history

Date	Revision	Changes
06-Aug-2014	1	First release.
01-Jul-2015	2	<p>Text and formatting changes throughout document</p> <p>Datasheet promoted from preliminary data to production data</p> <p>On cover page:</p> <ul style="list-style-type: none"> - updated <i>title description</i> - updated <i>features table</i> <p>In Section Electrical ratings:</p> <ul style="list-style-type: none"> - updated <i>Table Absolute maximum ratings</i> - updated <i>Table Thermal data</i> - updated <i>Table Avalanche characteristics</i> <p>In Section Electrical characteristics:</p> <ul style="list-style-type: none"> - updated and renamed <i>Table Static (was On/off states)</i> - updated <i>Table Dynamic</i> - updated <i>Table Switching times</i> - updated <i>Table Source-drain diode</i> <p>Added <i>Section 2.1 Electrical characteristics (curves)</i></p>
22-Aug-2019	3	<p>Modified Table 2. Thermal data.</p> <p>Minor text changes.</p>

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